Contents of Applied Physics A 58

This listing presents the papers in alphabetical order of the first author, subdivided into the sections "**Solids and Materials**: Physical and Chemical Properties" and "**Surfaces and Multilayers**: Growth, Modification, and Integration". The Author Index that follows covers **Applied Physics A** and **B**, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second and third columns contain the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The PACS numbers given in the fourth column may be used in conjunction with the PACS listing on the left to infer the topic of a paper.

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Infrared holographic recording in $LiNbO_3$:Cu.
Appl. Phys. A **58**/3, 291-295 (1994) PACS: 42.40 78.20 61.70

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Spectroscopic properties and excited-state relaxation dynamics of Er^{3+} in $LiNbO_3$.
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Self-organization of cavities under irradiation.
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Application of multipulse sequences in remote NQR.
Appl. Phys. A **58**/1, 63-65 (1994) PACS: 41.00

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Theory of solitary plastic waves: II. Lüders bands in single glide-oriented crystals.
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Temperature-induced rearrangement of the dislocation pattern of persistent slip bands in copper single crystals.
Appl. Phys. A **58**/3, 297-310 (1994)* PACS: 62.20M 81.40

Hsieh W.C., Su C.S.:
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Itoh Y., Murakami H.:
Defect study on electron irradiated GaAs by means of positron annihilation.
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Beam-coupling in tetragonal potassium tantalate-niobate crystals.
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The profile of layered materials reflected by glancing-incidence X-ray analysis.
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* In the March issue of Volume A **58** [Appl. Phys. A **58**/3 (1994)], there was unfortunately an error in pagination; all page numbers should have been 100 higher. In the present index the correct page numbers are given.